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# MMBT489LT1G

## High Current Surface Mount NPN Silicon Switching Transistor for Load Management in Portable Applications

### Features

- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

### MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ )

Rating	Symbol	Max	Unit
Collector-Emitter Voltage	$V_{CEO}$	30	Vdc
Collector-Base Voltage	$V_{CBO}$	50	Vdc
Emitter-Base Voltage	$V_{EBO}$	5.0	Vdc
Collector Current – Continuous	$I_C$	1.0	A
Collector Current – Peak	$I_{CM}$	2.0	A

### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation (Note 1) @ $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	310 2.5	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient (Note 1)	$R_{\theta JA}$	403	$^\circ\text{C}/\text{W}$
Total Device Dissipation (Note 2) @ $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	710 5.7	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	176	$^\circ\text{C}/\text{W}$
Total Device Dissipation (Single Pulse < 10 s)	$P_{D\text{single}}$	575	mW
Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

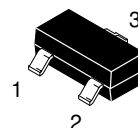
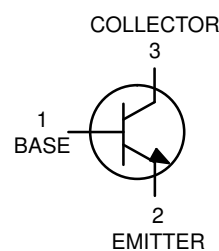
1. FR-4 @ Minimum Pad
2. FR-4 @ 1.0 X 1.0 inch Pad



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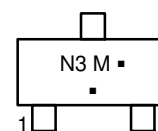
[www.onsemi.com](http://www.onsemi.com)

## 30 VOLTS, 2.0 AMPERES NPN TRANSISTOR



SOT-23 (TO-236)  
CASE 318  
STYLE 6

### MARKING DIAGRAM



N3 = Specific Device Code  
M = Date Code\*  
▪ = Pb-Free Package

(Note: Microdot may be in either location)  
\*Date Code orientation and/or overbar may vary depending upon manufacturing location.

### ORDERING INFORMATION

Device	Package	Shipping†
MMBT489LT1G	SOT-23 (Pb-Free)	3000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# MMBT489LT1G

## ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
<b>OFF CHARACTERISTICS</b>				
Collector–Emitter Breakdown Voltage ( $I_C = 10\text{ mA}$ , $I_B = 0$ )	$V_{(BR)CEO}$	30	–	Vdc
Collector–Base Breakdown Voltage ( $I_C = 0.1\text{ mA}$ , $I_E = 0$ )	$V_{(BR)CBO}$	50	–	Vdc
Emitter–Base Breakdown Voltage ( $I_E = 0.1\text{ mA}$ , $I_C = 0$ )	$V_{(BR)EBO}$	5.0	–	Vdc
Collector Cutoff Current ( $V_{CB} = 30\text{ Vdc}$ , $I_E = 0$ )	$I_{CBO}$	–	0.1	$\mu\text{A}$ dc
Collector–Emitter Cutoff Current ( $V_{CES} = 30\text{ Vdc}$ )	$I_{CES}$	–	0.1	$\mu\text{A}$ dc
Emitter Cutoff Current ( $V_{EB} = 4.0\text{ Vdc}$ )	$I_{EBO}$	–	0.1	$\mu\text{A}$ dc
<b>ON CHARACTERISTICS</b>				
DC Current Gain (Note 3) ( $I_C = 50\text{ mA}$ , $V_{CE} = 5.0\text{ V}$ ) ( $I_C = 0.5\text{ A}$ , $V_{CE} = 5.0\text{ V}$ ) ( $I_C = 1.0\text{ A}$ , $V_{CE} = 5.0\text{ V}$ )	$h_{FE}$	300 300 200	– 900 –	
Collector–Emitter Saturation Voltage (Note 3) ( $I_C = 1.0\text{ A}$ , $I_B = 100\text{ mA}$ ) ( $I_C = 0.5\text{ A}$ , $I_B = 50\text{ mA}$ ) ( $I_C = 0.1\text{ A}$ , $I_B = 1.0\text{ mA}$ )	$V_{CE(sat)}$	– – –	0.200 0.125 0.075	V
Base–Emitter Saturation Voltage (Note 3) ( $I_C = 1.0\text{ A}$ , $I_B = 0.1\text{ A}$ )	$V_{BE(sat)}$	–	1.1	V
Base–Emitter Turn–on Voltage (Note 3) ( $I_C = 1.0\text{ mA}$ , $V_{CE} = 2.0\text{ V}$ )	$V_{BE(on)}$	–	1.1	V
Cutoff Frequency ( $I_C = 100\text{ mA}$ , $V_{CE} = 5.0\text{ V}$ , $f = 100\text{ MHz}$ )	$f_T$	100	–	MHz
Output Capacitance ( $f = 1.0\text{ MHz}$ )	$C_{obo}$	–	15	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulsed Condition: Pulse Width = 300  $\mu\text{sec}$ , Duty Cycle  $\leq 2\%$

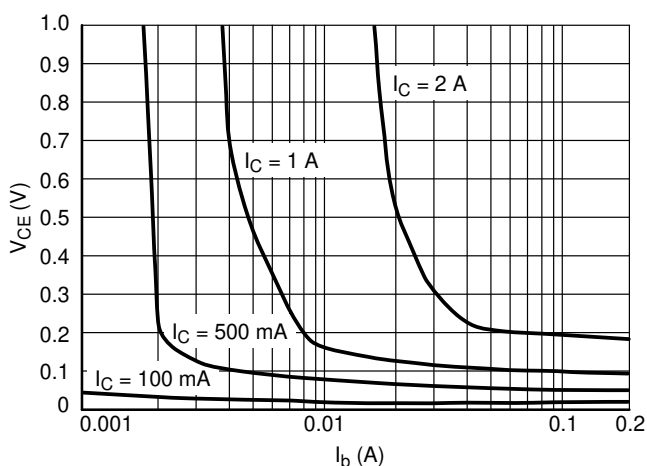


Figure 1.  $V_{CE}$  versus  $I_B$

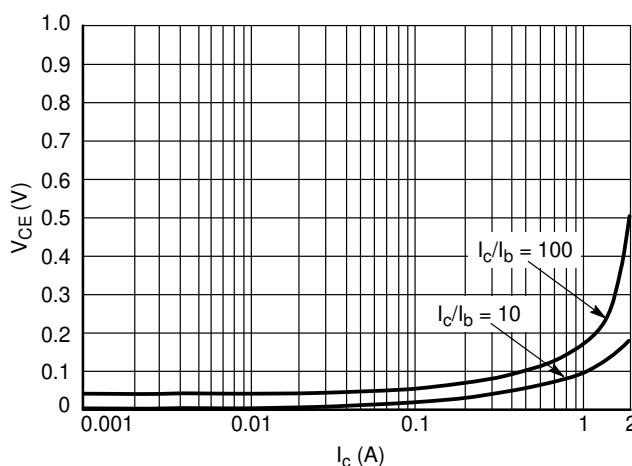


Figure 2.  $V_{CE}$  versus  $I_C$

# MMBT489LT1G

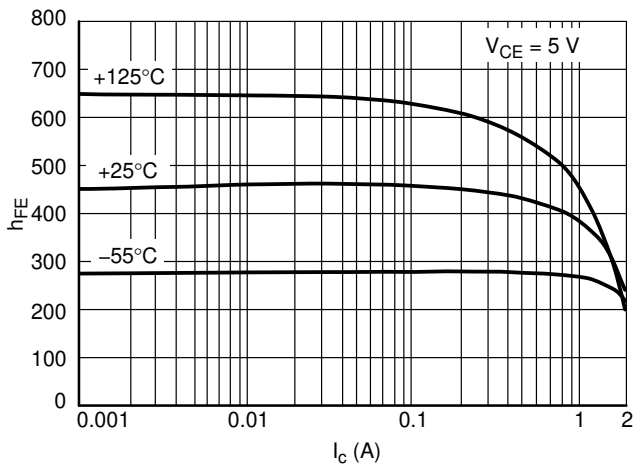


Figure 3.  $h_{FE}$  versus  $I_C$

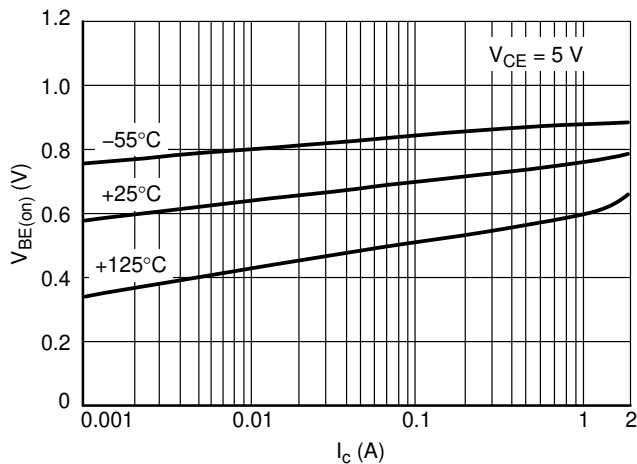


Figure 4.  $V_{BE(on)}$  versus  $I_C$

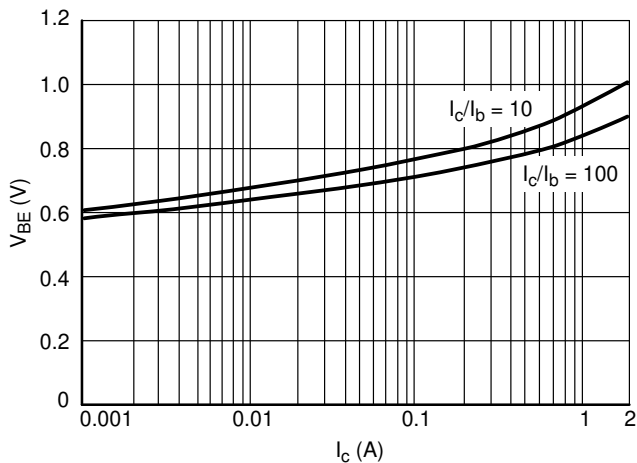


Figure 5.  $V_{BE(sat)}$  versus  $I_C$

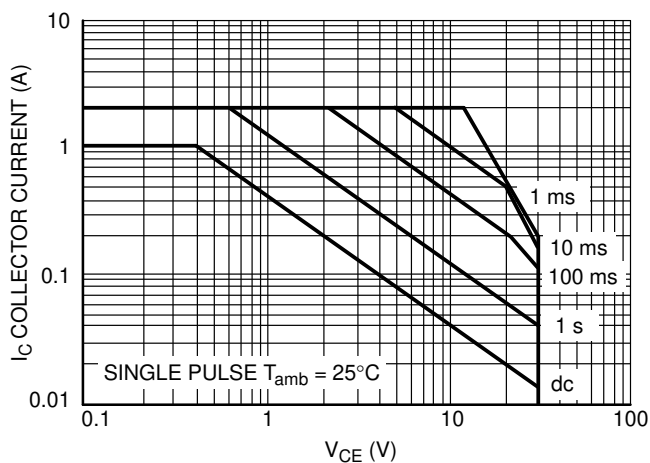


Figure 6. Safe Operating Area

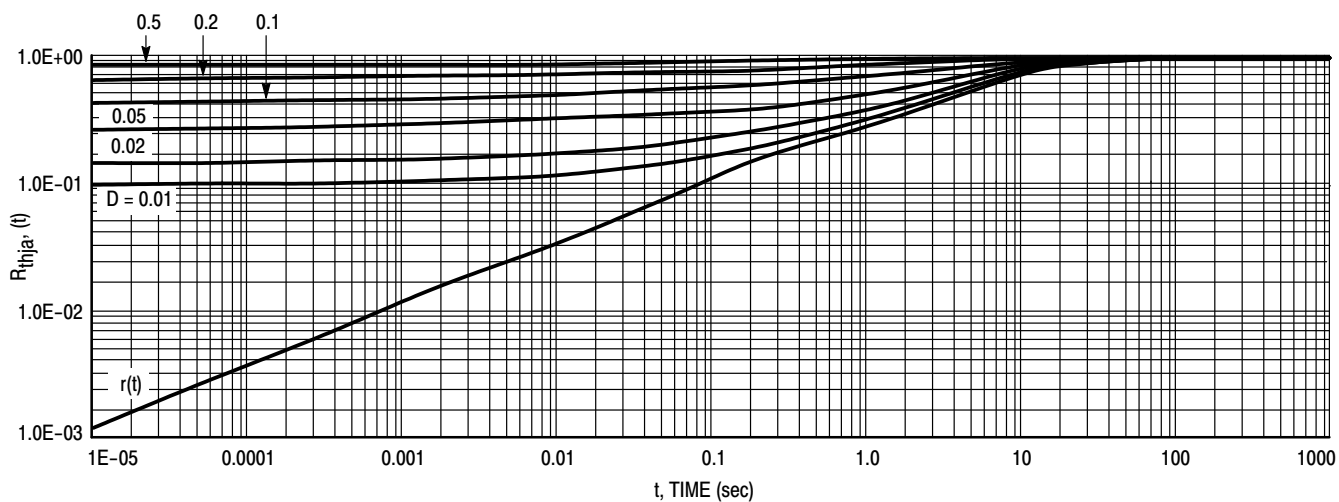
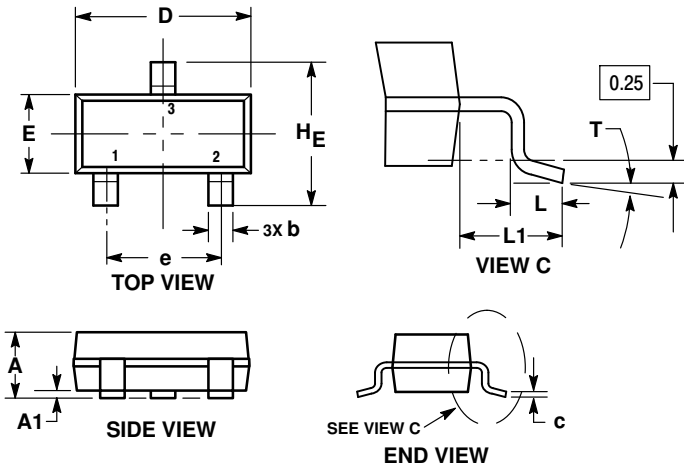


Figure 7. Normalized Thermal Response

# MMBT489LT1G

## PACKAGE DIMENSIONS

SOT-23 (TO-236)  
CASE 318-08  
ISSUE AR



**NOTES:**

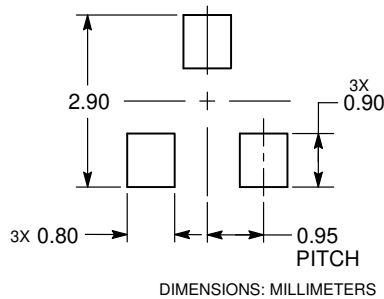
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
c	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
T	0°	---	10°	0°	---	10°

**STYLE 6:**

- PIN 1. BASE
- EMITTER
- COLLECTOR

### RECOMMENDED SOLDERING FOOTPRINT\*



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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